onsemi

Complementary Silicon High-Power Transistors

2N3055AG (NPN), MJ15015G (NPN), MJ15016G (PNP)

These PowerBase complementary transistors are designed for high power audio, stepping motor and other linear applications. These devices can also be used in power switching circuits such as relay or solenoid drivers, dc–to–dc converters, inverters, or for inductive loads requiring higher safe operating area than the 2N3055.

Features

• High Current-Gain - Bandwidth

MAXIMUM RATINGS (Note 1)

- Safe Operating Area
- These Devices are Pb-Free and are RoHS Compliant*

Rating	Symbol	Value	Unit
Collector–Emitter Voltage 2N3055AG MJ15015G, MJ15016G	V _{CEO}	60 120	Vdc
Collector–Base Voltage 2N3055AG MJ15015G, MJ15016G	V _{CBO}	100 200	Vdc
Collector–Emitter Voltage Base Reversed Biased 2N3055AG MJ15015G, MJ15016G	V _{CEV}	100 200	Vdc
Emitter-Base Voltage	V _{EBO}	7.0	Vdc
Collector Current – Continuous	۱ _C	15	Adc
Base Current	Ι _Β	7.0	Adc
Total Device Dissipation @ T _C = 25°C 2N3055AG MJ15015G, MJ15016G Derate above 25°C 2N3055AG MJ15015G, MJ15016G	P _D	115 180 0.65 1.03	W W W/°C W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Indicates JEDEC Registered Data. (2N3055A)

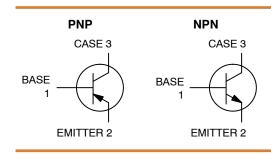
THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.52	0.98	°C/W

*For additional information on our Pb–Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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15 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60, 120 VOLTS – 115, 180 WATTS





MARKING DIAGRAMS \cap \cap 2N3055AG MJ1501xG AYWW AYWW MEX MFX Ο \bigcirc 2N3055A = Device Code MJ1501x = Device Code x = 5 or 6 G = Pb-Free Package А = Assembly Location Y Year = WW Work Week = MEX Country of Origin

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

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2N3055AG (NPN), MJ15015G (NPN), MJ15016G (PNP)

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic			Min	Max	Unit
OFF CHARACTERISTICS (Note 2)					
Collector–Emitter Sustaining Voltage (Note 3) ($I_C = 200 \text{ mAdc}, I_B = 0$)	2N3055AG MJ15015G, MJ15016G	V _{CEO(sus)}	60 120		Vdc
Collector Cutoff Current (V _{CE} = 30 Vdc, V _{BE(off)} = 0 Vdc) (V _{CE} = 60 Vdc, V _{BE(off)} = 0 Vdc)	2N3055AG MJ15015G, MJ15016G	I _{CEO}	- -	0.7 0.1	mAdc
Collector Cutoff Current (Note 3) (V _{CEV} = Rated Value, V _{BE(off)} = 1.5 Vdc)	2N3055AG MJ15015G, MJ15016G	I _{CEV}	-	5.0 1.0	mAdc
			- -	30 6.0	mAdc
Emitter Cutoff Current ($V_{EB} = 7.0 \text{ Vdc}, I_C = 0$)	2N3055AG MJ15015G, MJ15016G	I _{EBO}	-	5.0 0.2	mAdc
SECOND BREAKDOWN (Note 3)					
Second Breakdown Collector Current with Base F (t = 0.5 s non-repetitive) (V _{CE} = 60 Vdc)	Forward Biased 2N3055AG MJ15015G, MJ15016G	I _{S/b}	1.95 3.0		Adc
ON CHARACTERISTICS (Note 2 and 3)					
DC Current Gain (I _C = 4.0 Adc, V _{CE} = 2.0 Vdc) (I _C = 4.0 Adc, V _{CE} = 4.0 Vdc) (I _C = 10 Adc, V _{CE} = 4.0 Vdc)		h _{FE}	10 20 5.0	70 70 -	-
Collector-Emitter Saturation Voltage ($I_C = 4.0$ Adc, $I_B = 400$ mAdc) ($I_C = 10$ Adc, $I_B = 3.3$ Adc) ($I_C = 15$ Adc, $I_B = 7.0$ Adc)		V _{CE(sat)}	- - -	1.1 3.0 5.0	Vdc
Base-Emitter On Voltage (I _C = 4.0 Adc, V _{CE} = 4.0 Vdc)			0.7	1.8	Vdc
DYNAMIC CHARACTERISTICS (Note 3)		•		•	•
Current–Gain – Bandwidth Product ($I_C = 1.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}, f = 1.0 \text{ MHz}$)	2N3055AG, MJ15015G MJ15016G	f _T	0.8 2.2	6.0 18	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C _{ob}	60	600	pF
SWITCHING CHARACTERISTICS (2N3055AG o	nly) (Note 3)				
RESISTIVE LOAD					
Delay Time		t _d	-	0.5	μs
Rise Time	(V _{CC} = 30 Vdc, I _C = 4.0 Adc, I _{B1} = I _{B2} = 0.4 Adc,	t _r	-	4.0	μs
Storage Time	$t_p = 25 \ \mu s \ Duty \ Cycle \le 2\%$	t _s	_	3.0	μs
Fall Time		t _f	_	6.0	μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.
Indicates JEDEC Registered Data. (2N3055A)

2N3055AG (NPN), MJ15015G (NPN), MJ15016G (PNP)

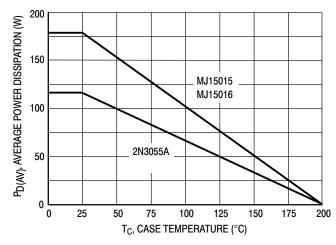
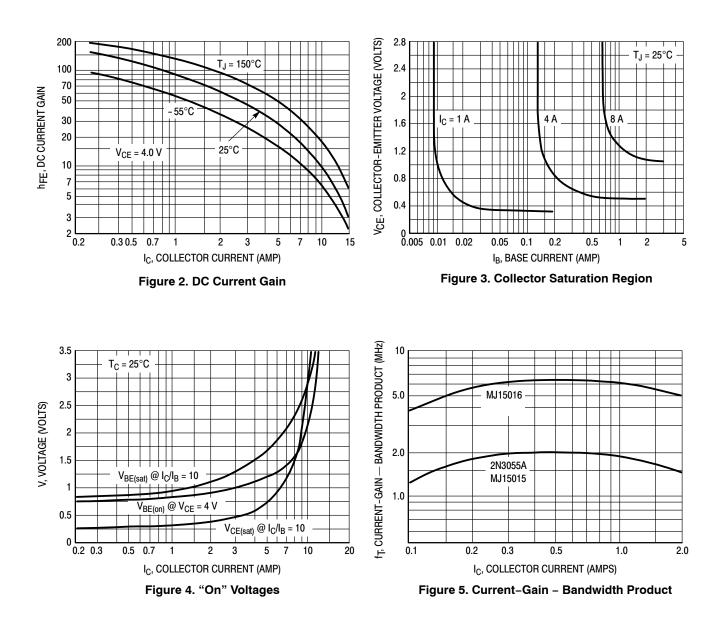


Figure 1. Power Derating



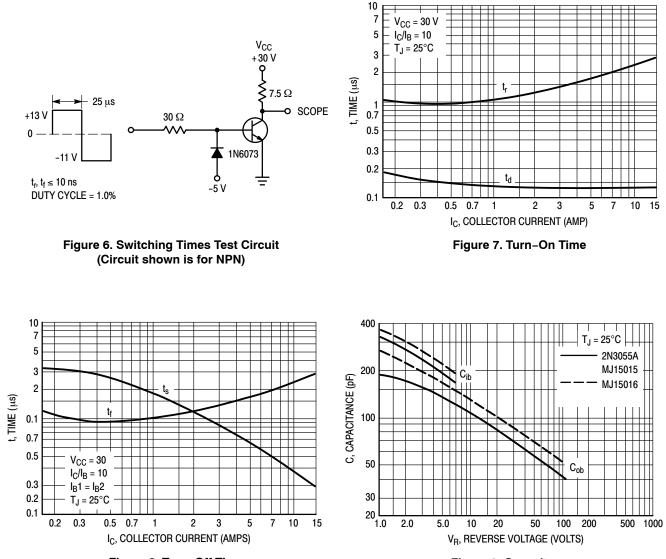
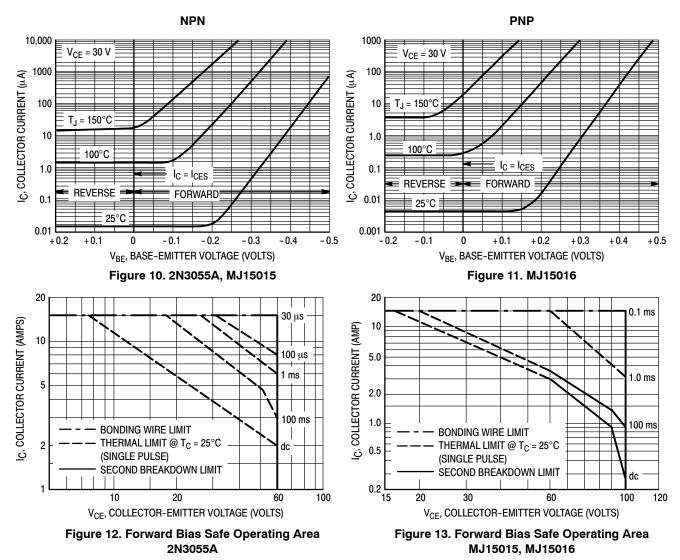


Figure 8. Turn-Off Times

Figure 9. Capacitances

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COLLECTOR CUT-OFF REGION



There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe Operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 12 and 13 is based on $T_C = 25^{\circ}C$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated for temperature according to Figure 1.

Device	Package	Shipping
2N3055AG	TO–204 (Pb–Free)	100 Units / Tray
MJ15015G	TO-204 (Pb-Free)	100 Units / Tray
MJ15016G	TO-204 (Pb-Free)	100 Units / Tray

ORDERING INFORMATION

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TO-204 (TO-3) CASE 1-07 ISSUE Z DATE 10 MAR 2000 SCALE 1:1 NOTES: Δ 1. DIMENSIONING AND TOLERANCING PER ANSI ٠N Y14.5M. 1982. ¥ 2. CONTROLLING DIMENSION: INCH. 3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY. С E -T- SEATING PLANE MILLIMETERS Łκ INCHES → 🖛 D 2 PL MIN MAX MIN MAX DIM Α 1.550 REF 39.37 REF $| \oplus | \oslash 0.13 (0.005)$ \square T Q \square Y \square B
 -- 1.050
 -- 26.67

 0.250
 0.335
 6.35
 8.51

 D
 0.038
 0.043
 0.97

 E
 0.055
 0.070
 1.40
 1.09 1.40 1.77 -Y-1-> v G 0.430 BSC 10.92 BSC
 H
 0.215 BSC
 5.46 BSC

 K
 0.440
 0.480
 11.18
 12.19
 2**⊕** G ന് в 0.665 BSC 16.89 BSC L Ĥ
 N
 -- 0.830
 -- 21.08

 Q
 0.151
 0.165
 3.84
 4.19
 \oplus Å
 U
 1.187 BSC
 30.15 BSC

 V
 0.131
 0.188
 3.33
 4.77
 -Q-⊕ Ø 0.13 (0.005) M T Y M STYLE 3: PIN 1. GATE 2. SOURCE STYLE 5: PIN 1. CATHODE 2. EXTERNAL TRIP/DELAY STYLE 1: PIN 1. BASE STYLE 4: PIN 1. GROUND STYLE 2: PIN 1. BASE 2. COLLECTOR 2 FMITTER 2 INPUT CASE: COLLECTOR CASE: EMITTER CASE: DRAIN CASE: OUTPUT CASE: ANODE STYLE 6: STYLE 7: STYLE 8: STYLE 9: PIN 1. GATE 2. EMITTER PIN 1. ANODE 2. OPEN PIN 1. CATHODE #1 2. CATHODE #2 PIN 1. ANODE #1 2. ANODE #2

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DESCRIPTION:	TO-204 (TO-3)		PAGE 1 OF 1

CASE: ANODE

CASE: CATHODE

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CASE: COLLECTOR

CASE: CATHODE

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